

40V +175°C P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max Tc = +25°C
-40V	25mΩ @ V _{GS} = -10V	-52A
-400	45mΩ @ V _{GS} = -4.5V	-38A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

Reverse-polarity protections

- Power-management functions
- **DC-DC** converters

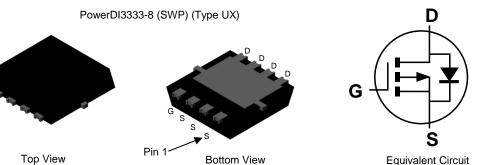
Features and Benefits

- Rated to +175°C—Ideal for High Ambient Temperature • Environments
- Low RDS(ON)-Ensures Minimal On-State Losses .
- Small Form Factor Thermally Efficient Package Enables Higher **Density End Products**
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Products
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMPH4026SFVWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: PowerDI[®]3333-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.03 grams (Approximate)



Ordering Information (Note 4)

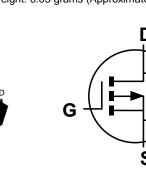
Part Number	Package	Packing		
Fait Nulliper	Fachaye	Qty.	Carrier	
DMPH4026SFVWQ-7	PowerDI3333-8 (SWP) (Type UX)	2000	Tape & Reel	
DMPH4026SFVWQ-13	PowerDI3333-8 (SWP) (Type UX)	3000	Tape & Reel	

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. Notes: 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and

<1000ppm antimony compounds.

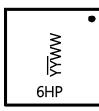
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.







Marking Information



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	-40	V		
Gate-Source Voltage	Vgss	±20	V		
Continuous Drain Current V _{GS} = -10V (Note 5)	Steady State	Tc = +25°C Tc = +100°C	ID	-52 -38	A
Continuous Drain Current V _{GS} = -10V (Note 6)	Steady State	T _A = +25°C T _A = +100°C	ID	-9.3 -6.6	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			Ідм	-208	A
Maximum Body Diode Continuous Current (Note 5)	ls	-52	A		
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)			Ism	-208	А
Avalanche Current L = 0.3mH			las	-27	А
Avalanche Energy L = 0.3mH			Eas	109	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 7)	T _A = +25°C	PD	2.0	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	Reja	75.2	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	PD	3.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	38.4	°C/W
Thermal Resistance, Junction to Case (Note 5)		R _{eJC}	1.25	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Notes: 5. Thermal resistance from junction to soldering point (on the exposed drain pad).

6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

7. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.



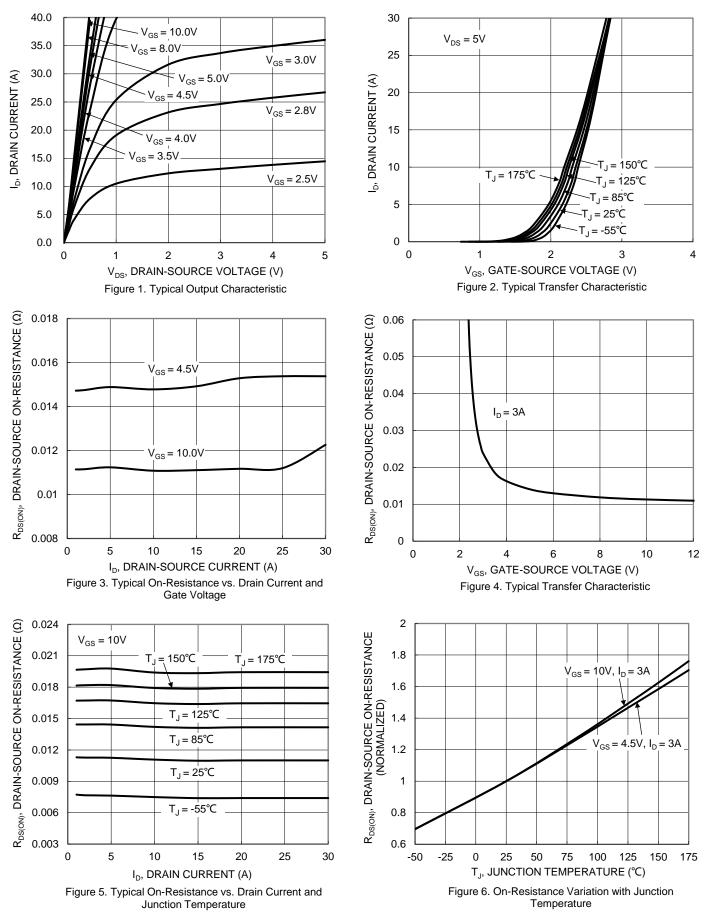
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BVDSS	-40	_		V	$V_{GS} = 0V, I_D = -250 \mu A$	
Zero Gate Voltage Drain Current	IDSS	_	—	-1	μA	V _{DS} = -40V, V _{GS} = 0V	
Gate-Source Leakage	lgss	_	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	Vgs(th)	-0.8	—	-1.8	V	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	
Static Drain-Source On-Resistance	Desser	_	11.1	25	mΩ	$V_{GS} = -10V, I_D = -3A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	14.6	45	11122	$V_{GS} = -4.5V, I_D = -3A$	
Diode Forward Voltage	Vsd	_	-0.7	-1	V	VGS = 0V, IS = -1A	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	_	2064	_	pF		
Output Capacitance	Coss	_	212	_	pF	− V _{DS} = -20V, V _{GS} = 0V − f = 1MHz	
Reverse Transfer Capacitance	Crss	_	183	_	pF		
Gate Resistance	Rg	_	2.5	_	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz	
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	23.5	_	nC		
Total Gate Charge (V _{GS} = -10V)	Qg		45.8	_	nC	V _{DS} = -20V, I _D = -3A	
Gate-Source Charge	Qgs		5		nC	VDS20V, ID3A	
Gate-Drain Charge	Q _{gd}	_	6.7	—	nC		
Turn-On Delay Time	td(ON)	_	4.3	_	ns		
Turn-On Rise Time	tR	_	4.7	_	ns	V _{DD} = -20V, V _{GS} = -10V	
Turn-Off Delay Time	tD(OFF)		71.8	_	ns	I _D = -3A	
Turn-Off Fall Time	tF	_	23.9		ns	7	
Body Diode Reverse Recovery Time	trr	_	17.3		ns	Is = -3A, dl/dt = 100A/µs	
Body Diode Reverse Recovery Charge	Qrr	_	8.7		nC	Is = -3A, dI/dt = 100A/µs	

Notes: 8. Short duration pulse test used to minimize self-heating effect. 9. Guaranteed by design. Not subject to product testing.



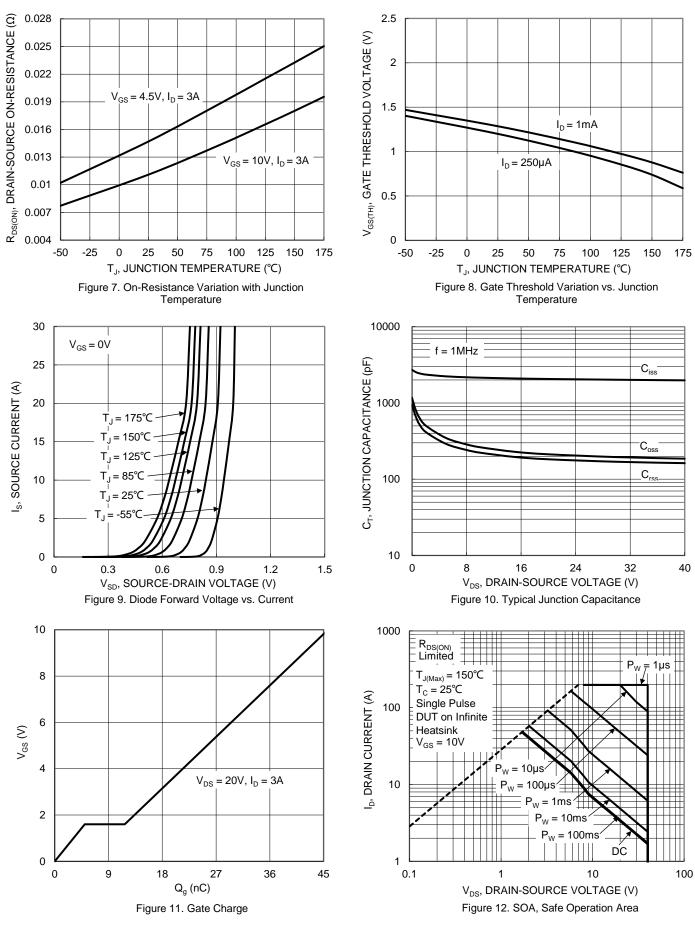
DMPH4026SFVWQ



DMPH4026SFVWQ Document number: D45177 Rev. 3 - 2

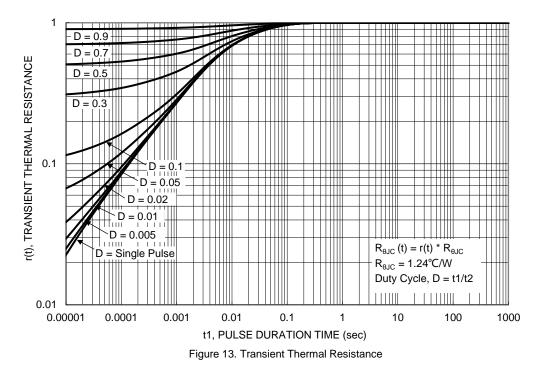


DMPH4026SFVWQ



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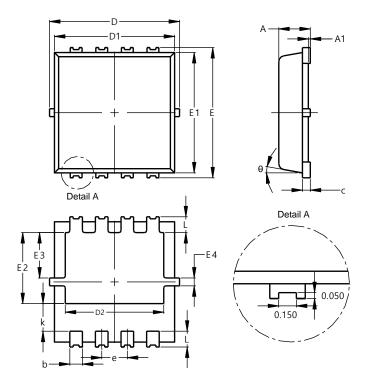






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



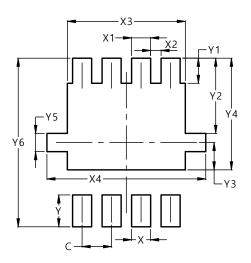
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PowerDI3333-8 (SWF)	(iype	UA)

Pov	PowerDI3333-8 (SWP)					
	(Type UX)					
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	-	0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700



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